IRF241, IRF243 File Number **1584**

Power MOS Field-Effect Transistors

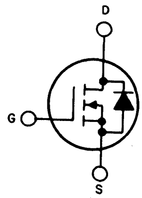
N-Channel Enhancement-Mode Power Field-Effect Transistors

16A and 18A, 150V

$r_{DS}(on)$ = 0.18 Ω and 0.22 Ω

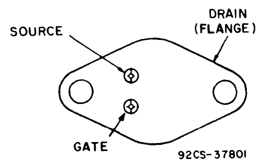
Features:
- *SOA is power-dissipation limited*
- *Nanosecond switching speeds*
- *Linear transfer characteristics*
- *High input impedance*
- *Majority carrier device*

N-CHANNEL ENHANCEMENT MODE



TERMINAL DIAGRAM

TERMINAL DESIGNATION



JEDEC TO-204AE

The IRF241 and IRF243 are n-channel enhancement-mode silicon-gate power field-effect transistors designed for applications such as switching regulators, switching converters, motor drivers, relay drivers, and drivers for high-power bipolar switching transistors requiring high speed and low gate-drive power. These types can be operated directly from integrated circuits.

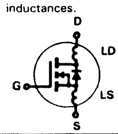
The IRF-types are supplied in the JEDEC TO-204AE steel package.

Absolute Maximum Ratings

	Parameter	IRF241	IRF243	Units
V_{DS}	Drain - Source Voltage ①	150	150	V
V_{DGR}	Drain - Gate Voltage (R_{GS} = 20 KΩ) ①	150	150	V
I_D @ T_C = 25°C	Continuous Drain Current	18	16	A
I_D @ T_C = 100°C	Continuous Drain Current	11	10	A
I_{DM}	Pulsed Drain Current ③	72	64	A
V_{GS}	Gate - Source Voltage	± 20		V
P_D @ T_C = 25°C	Max. Power Dissipation	125 (See Fig. 14)		W
	Linear Derating Factor	1.0 (See Fig. 14)		W/°C
I_{LM}	Inductive Current, Clamped	(See Fig. 15 and 16) L = 100μH 72 | 72 | 64 | 64		A
T_J T_{stg}	Operating Junction and Storage Temperature Range	-55 to 150		°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)		°C

IRF241, IRF243

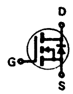
Electrical Characteristics @T_C = 25°C (Unless Otherwise Specified)

Parameter	Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS} Drain - Source Breakdown Voltage	IRF241 IRF243	150	–	–	V	V_{GS} = 0V I_D = 250μA
$V_{GS(th)}$ Gate Threshold Voltage	ALL	2.0	–	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
I_{GSS} Gate-Source Leakage Forward	ALL	–	–	100	nA	V_{GS} = 20V
I_{GSS} Gate-Source Leakage Reverse	ALL	–	–	-100	nA	V_{GS} = -20V
I_{DSS} Zero Gate Voltage Drain Current	ALL	–	–	250	μA	V_{DS} = Max. Rating, V_{GS} = 0V
		–	–	1000	μA	V_{DS} = Max. Rating x 0.8, V_{GS} = 0V, T_C = 125°C
$I_{D(on)}$ On-State Drain Current ②	IRF241	18	–	–	A	V_{DS} > $I_{D(on)}$ x $R_{DS(on)}$ max., V_{GS} = 10V
	IRF243	16	–	–	A	
$R_{DS(on)}$ Static Drain-Source On-State Resistance ②	IRF241	–	0.14	0.18	Ω	V_{GS} = 10V, I_D = 10A
	IRF243	–	0.20	0.22	Ω	
g_{fs} Forward Transconductance ②	ALL	6.0	9.0	–	S (℧)	V_{DS} > $I_{D(on)}$ x $R_{DS(on)}$ max., I_D = 10A
C_{iss} Input Capacitance	ALL	–	1275	1600	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0 MHz See Fig. 10
C_{oss} Output Capacitance	ALL	–	500	750	pF	
C_{rss} Reverse Transfer Capacitance	ALL	–	160	300	pF	
$t_{d(on)}$ Turn-On Delay Time	ALL	–	16	30	ns	V_{DD} ≈ 75V, I_D = 10A, Z_o = 4.7Ω See Fig. 17 (MOSFET switching times are essentially independent of operating temperature.)
t_r Rise Time	ALL	–	27	60	ns	
$t_{d(off)}$ Turn-Off Delay Time	ALL	–	40	80	ns	
t_f Fall Time	ALL	–	31	60	ns	
Q_g Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	–	43	60	nC	V_{GS} = 10V, I_D = 22A, V_{DS} = 0.8 Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)
Q_{gs} Gate-Source Charge	ALL	–	16	–	nC	
Q_{gd} Gate-Drain ("Miller") Charge	ALL	–	27	–	nC	
L_D Internal Drain Inductance	ALL	–	5.0	–	nH	Measured between the contact screw on header that is closer to source and gate pins and center of die. — Modified MOSFET symbol showing the internal device inductances. 
L_S Internal Source Inductance	ALL	–	12.5	–	nH	Measured from the source pin, 6 mm (0.25 in.) from header and source bonding pad.

Thermal Resistance

R_{thJC} Junction-to-Case	ALL	–	–	1.0	°C/W	
R_{thCS} Case-to-Sink	ALL	–	0.1	–	°C/W	Mounting surface flat, smooth, and greased.
R_{thJA} Junction-to-Ambient	ALL	–	–	30	°C/W	Free Air Operation

Source-Drain Diode Ratings and Characteristics

I_S Continuous Source Current (Body Diode)	IRF241	–	–	18	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier. 
	IRF243	–	–	16	A	
I_{SM} Pulse Source Current (Body Diode) ③	IRF241	–	–	72	A	
	IRF243	–	–	64	A	
V_{SD} Diode Forward Voltage ②	IRF241	–	–	2.0	V	T_C = 25°C, I_S = 18A, V_{GS} = 0V
	IRF243	–	–	1.9	V	T_C = 25°C, I_S = 16A, V_{GS} = 0V
t_{rr} Reverse Recovery Time	ALL	–	650	–	ns	T_J = 150°C, I_F = 18A, dI_F/dt = 100A/μs
Q_{RR} Reverse Recovered Charge	ALL	–	4.1	–	μC	T_J = 150°C, I_F = 18A, dI_F/dt = 100A/μs
t_{on} Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L_S + L_D.				

①T_J = 25°C to 150°C. ②Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%. ③ Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).

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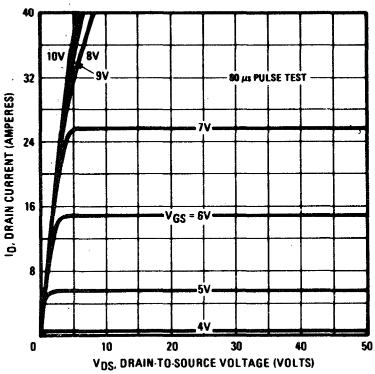

Fig. 1 — Typical Output Characteristics

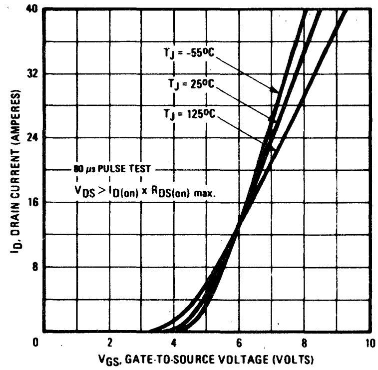

Fig. 2 — Typical Transfer Characteristics

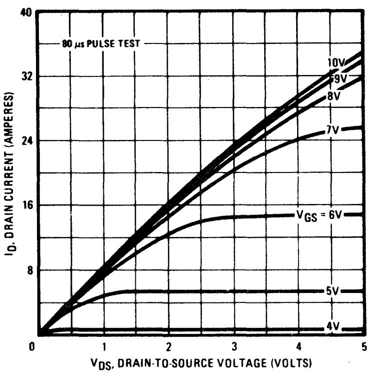

Fig. 3 — Typical Saturation Characteristics

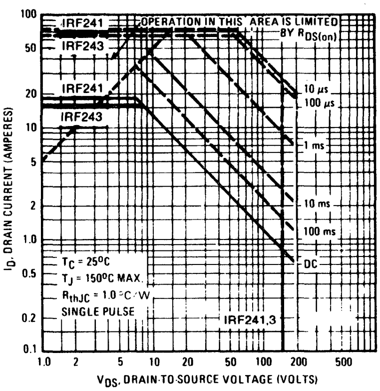

Fig. 4 — Maximum Safe Operating Area

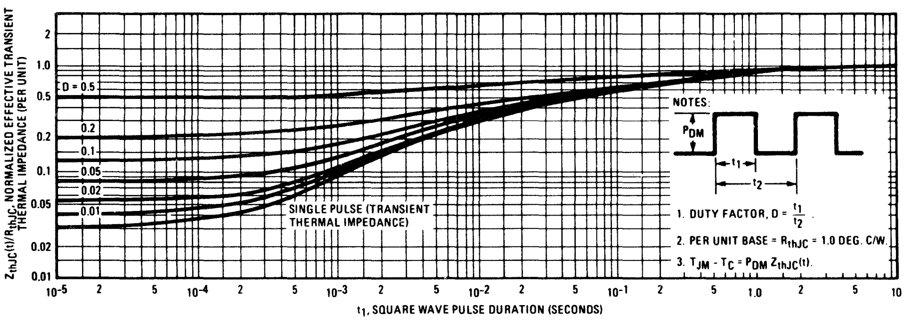

Fig. 5 — Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

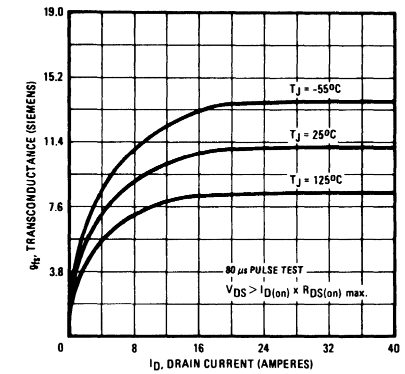

Fig. 6 — Typical Transconductance Vs. Drain Current

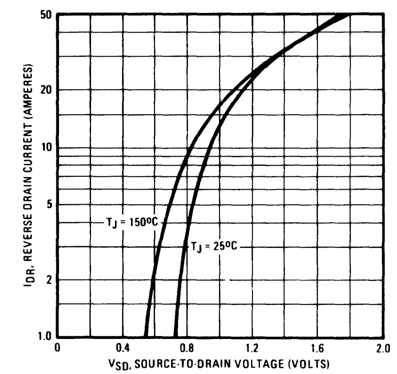

Fig. 7 — Typical Source-Drain Diode Forward Voltage

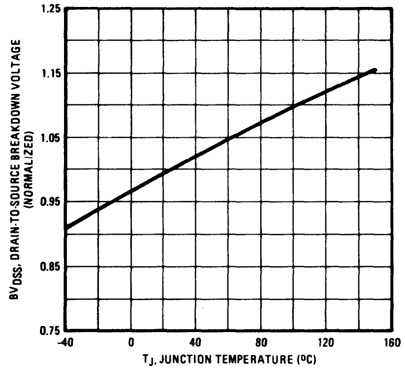

Fig. 8 — Breakdown Voltage Vs. Temperature

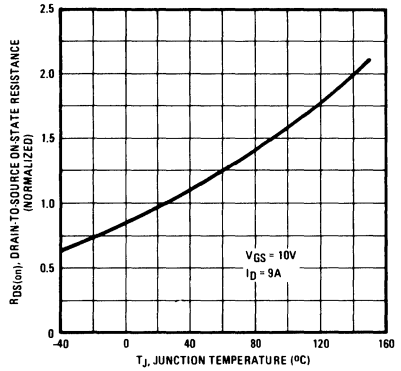

Fig. 9 — Normalized On-Resistance Vs. Temperature

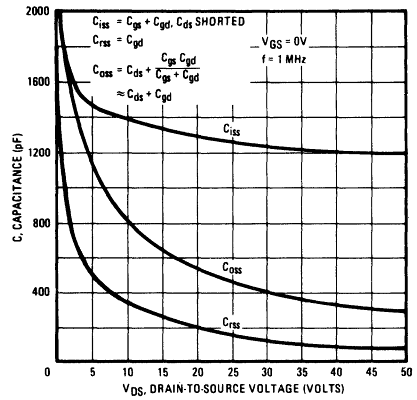

Fig. 10 — Typical Capacitance Vs. Drain-to-Source Voltage

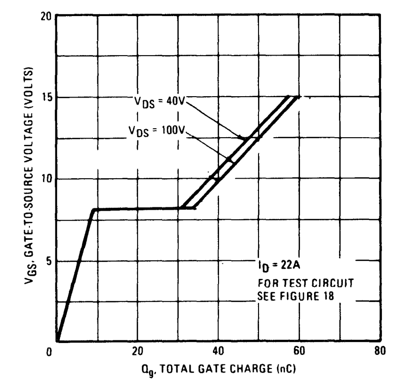

Fig. 11 — Typical Gate Charge Vs. Gate-to-Source Voltage

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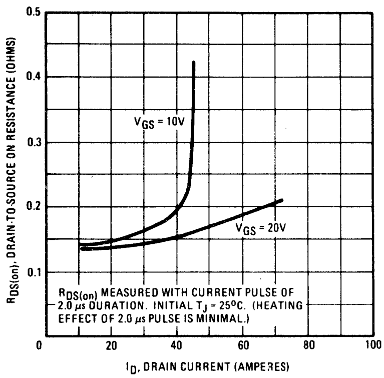

Fig. 12 – Typical On-Resistance Vs. Drain Current

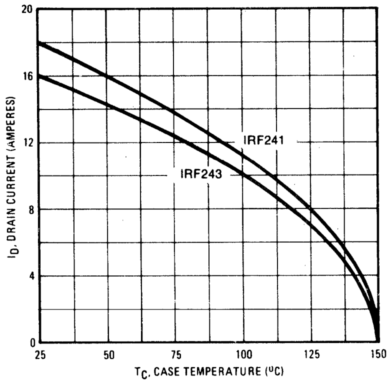

Fig. 13 – Maximum Drain Current Vs. Case Temperature

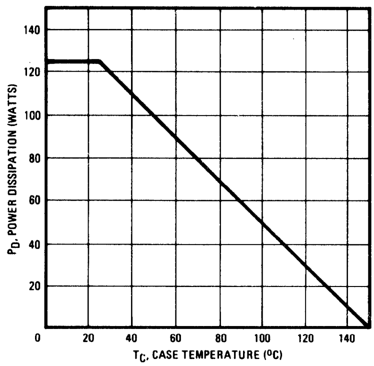

Fig. 14 – Power Vs. Temperature Derating Curve

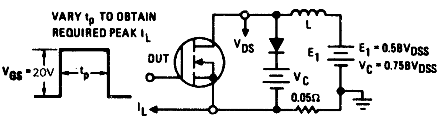

Fig. 15 – Clamped Inductive Test Circuit

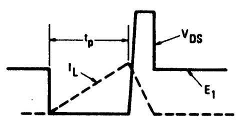

Fig. 16 – Clamped Inductive Waveforms

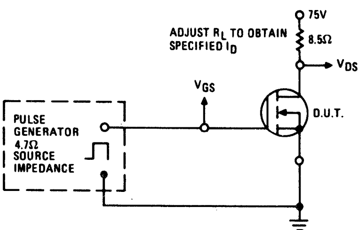

Fig. 17 – Switching Time Test Circuit

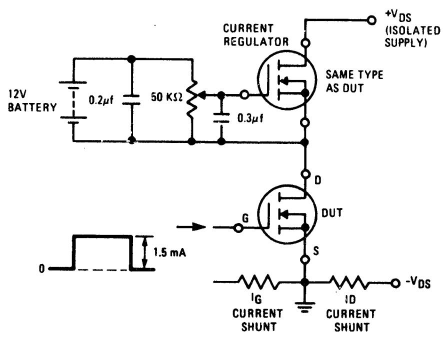

Fig. 18 – Gate Charge Test Circuit